

isc Silicon NPN RF Transistor

2SC5006

DESCRIPTION

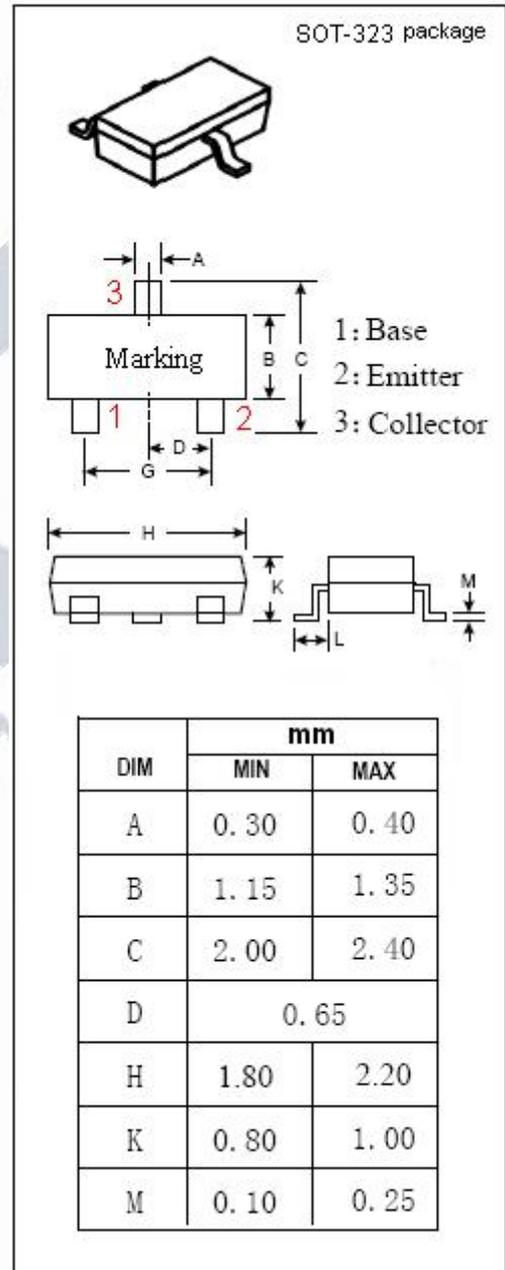
- Low Voltage Use
- Ultra Super Mini Mold Package
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in low noise and small signal amplifiers from VHF band to UHF band

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	20	V
V _{CEO}	Collector-Emitter Voltage	12	V
V _{EBO}	Emitter-Base Voltage	3	V
I _c	Collector Current-Continuous	100	mA
P _c	Collector Power Dissipation @T _c =25°C	125	mW
T _J	Max.Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-60~150	°C



isc Silicon NPN RF Transistor**2SC5006****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified, Pulse Measurement PW ≤ 350 μs, Duty Cycle ≤ 2 %**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I _{CB0}	Collector Cutoff Current	V _{CB} = 10V; I _E = 0			1	μ A
I _{EB0}	Emitter Cutoff Current	V _{EB} = 1V; I _C = 0			1	μ A
h _{FE}	DC Current Gain	I _C = 7mA; V _{CE} = 3V	80		160	
f _T	Current-Gain—Bandwidth Product	I _C = 7mA; V _{CE} = 3V	3.0			GHz
C _{re}	Feed-Back Capacitance	I _E = 0; V _{CB} = 3V; f= 1.0MHz			1.5	pF
S _{21e} ²	Insertion Power Gain	I _C = 7mA; V _{CE} = 3V; f= 1.0GHz	7			dB
NF	Noise Figure	I _C = 7mA; V _{CE} = 3V; f= 1.0GHz			2.5	dB